

WHAT IS CLAIMED IS:

1 1. An optical waveguide device, comprising:  
2 a substrate;  
3 at least one optical waveguide disposed in said substrate;  
4 a first conductive thin film layer placed in the vicinity of  
5 or on the top of said optical waveguide in said substrate and  
6 containing an oxide; and  
7 a second conductive thin film layer laminated on said first  
8 thin film layer and exhibiting acidic or neutral characteristics  
9 in its oxidized condition.

1 2. An optical waveguide device as claimed in claim 1,  
2 wherein:  
3 said first thin film layer contains an indium oxide (ITO).

1 3. An optical waveguide device as claimed in claim 1,  
2 wherein:  
3 said second thin film layer contains chromium.

1 4. An optical waveguide device as claimed in claim 1,  
2 wherein:  
3 a protective film is formed on at least one exposed surface  
4 of each of said first thin film layer and said second thin film  
5 layer.

1 5. An optical waveguide device as claimed in claim 1,  
2 wherein:

3 a third conductive thin film layer exhibiting neutral  
4 characteristics is formed on the surface of said second thin film  
5 layer.

1 6. An optical waveguide device as claimed in claim 5,  
2 wherein:  
3 said third thin film layer contains gold.

1 7. An optical waveguide device as claimed in claim 1,  
2 wherein:  
3 a protective film is formed over the whole exposed surface  
4 of an electrode composed of said first thin film layer, said second  
5 thin film layer, and said third thin film layer.

1 8. An optical waveguide device as claimed in claim 1,  
2 wherein:  
3 said substrate is fabricated from a lithium niobate ( $\text{LiNbO}_3$ )  
4 substrate;

5 said optical waveguide is disposed on said lithium niobate  
6 substrate in such a manner that two Mach-Zehnder type directional  
7 couplers are formed, and further a phase shifter is formed in  
8 between these directional couplers; and

9 said phase shifter is provided with an electrode of a structure  
10 containing said first thin film layer and said second thin film  
11 layer, whereby an electric field produced in response to a voltage  
12 applied to said electrode is given to said optical waveguide to  
13 function as a variable optical attenuator.

1           9. An optical waveguide device as claimed in claim 1,  
2 wherein:

3           said second thin film layer is provided with a third conductive  
4 thin film layer laminated thereon and exhibiting neutral  
5 characteristics in its oxidized condition.

1           10. An optical waveguide device as claimed in claim 1,  
2 wherein:

3           said first thin film layer is a thin film layer of indium oxide  
4 to which tin has been added (ITO); and

5           said second thin film layer is a chromium thin film layer.

1           11. An optical waveguide device as claimed in claim 9,  
2 wherein:

3           said third thin film layer is a gold thin film layer.

1           12. A process for the production of an optical waveguide  
2 device, comprising the steps of:

3           forming at least one optical waveguide in an LN (lithium  
4 niobate) substrate;

5           forming an ITO film on said optical waveguide and the surface  
6 of said LN substrate;

7           forming a photoresist on said ITO film to conduct a patterning  
8 operation;

9           removing unnecessary portions of said ITO film by means of  
10 etching with use of said photoresist as a mask to form the ITO  
11 pattern;

12          removing the photoresist on said ITO pattern;

13       forming a chromium thin film having a thinner film thickness  
14   than that of said ITO film on the surface of said ITO pattern and  
15   an exposed surface of said substrate;  
16       applying a photoresist on said chromium thin film;  
17       removing unnecessary portions of said chromium thin film by  
18   means of etching; and  
19       removing the photoresist remained on said chromium thin film  
20   after said etching.

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